

# isc N-Channel MOSFET Transistor

# IXTA140N12T2

#### • FEATURES

- Static drain-source on-resistance: R<sub>DS</sub>(on) ≤ 10mΩ@V<sub>GS</sub>=10V
- Fully characterized avalanche voltage and current
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### APPLICATION

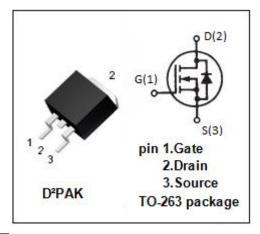
- DC/DC Converters
- · High Speed Power Switching Applications

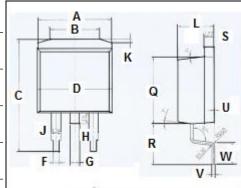
# • ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>DSS</sub>	Drain-Source Voltage	120	V	
V <sub>GS</sub>	Gate-Source Voltage	±20	o v	
I <sub>D</sub>	Drain Current-Continuous	140	А	
I <sub>DM</sub>	Drain Current-Single Pulsed	350	А	
P <sub>D</sub>	Total Dissipation @Tc=25℃	577	W	
Tj	Operating Junction Temperature	-55~175	°C	
T <sub>stg</sub>	Storage Temperature	-55~175	°C	

### • THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th(j-c)</sub>	Junction-to-case thermal resistance	0.26	°C/W





	mm		
DIM	MIN	MAX	
Α	10		
В	6.6	6.8	
C	15.23	15.25	
D	10.15	10.17	
F	0.76	0.78	
G	1.26	1.28	
Н	1.4	1.6	
J	1.33	1.35	
K	0.4	0.6	
L	4.6	4.8	
0	8.69	8.71	
R	5.28	5.30	
S	1.26	1.28	
U	0.0	0.2	
V	0.37	0.39	
W	2.80	2.82	



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### **IXTA140N12T2**

#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0V; ID = 250 μ A	120		V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; ID = 250 μ A	2.5	4.5	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> = 70A		10	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> =0V		±200	nA
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> = V <sub>DSS</sub> ; V <sub>GS</sub> = 0V		10	- μ А
		V <sub>DS</sub> = V <sub>DSS</sub> ; V <sub>GS</sub> = 0V;T <sub>J</sub> = 150°C		500	
VsD	Diode forward voltage	I <sub>F</sub> = 140A; V <sub>GS</sub> = 0V		1.4	V



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